		tin sel		
L Number	Hits	Search Text	DB	Time stamp
1	1	conduct\$3 and 6172732.pn.	USPAT	2004/02/20 20:57
2	1	(data or gate) and (conduct\$3 and	USPAT	2004/02/20
3 `	0	6172732.pn.) insulting and (conduct\$3 and	USPAT	21:57 2004/02/20 21:58
4	1	6172732.pn.) insulating and (conduct\$3 and	USPAT	2004/02/20
5	1	6172732.pn.) insulating and 5757450.pn.	USPAT	2004/02/20
6	1	substrate\$1 and (insulating and 5757450.pn.)	USPAT	2004/02/20
7	1	(metal\$3 or conduct\$3) and (substrate\$1 and (insulating and 5757450.pn.))	USPAT	2004/02/20
8	1	(insulating and 5757450.pn.) and film	USPAT	2004/02/20
9	1	(metal\$3 or conduct\$3) and ((insulating and 5757450.pn.) and film)	USPAT	2004/02/20
10	1	I	USPAT	2004/02/20
11	1	substrate\$1 and (film and (insulating and (conduct\$3 and 6172732.pn.)))	USPAT	2004/02/20
12	222945	capacitor\$1	USPAT	2004/02/20
13	0	(conduct\$3 and 6172732.pn.) and capacitor\$1	USPAT	2004/02/20
14	0	(conduct\$3 and 6172732.pn.) and (insulating and 5757450.pn.)	USPAT	2004/02/20 23:21
15	6336	plurality adj capacitor\$1	USPAT; US-PGPUB;	2004/02/20
			EPO; JPO; DERWENT;	
16	145501	liquid adj crystal adj device or lcd	IBM_TDB USPAT;	2004/02/20
			US-PGPUB; EPO; JPO;	23:23
17	10		DERWENT; IBM_TDB	2004/02/02
17	19	coductive adj layer\$1	USPAT; US-PGPUB;	2004/02/20 23:23
			EPO; JPO; DERWENT;	
18	3687	interconnection adj line\$1	IBM_TDB USPAT;	2004/02/20
		, i	US-PGPUB; EPO; JPO;	23:23
19	100160	andusting add 3 ares 63	DERWENT; IBM_TDB	2004/02/22
19	108169	conductive adj layer\$1	USPAT; US-PGPUB;	2004/02/20 23:24
			EPO; JPO; DERWENT;	
20	97	1 12 1 12 1 12 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB USPAT;	2004/02/20
		(conductive adj layer\$1)	US-PGPUB; EPO; JPO; DERWENT;	23:25
21	21	(liquid adj crystal adj device or lcd)	IBM_TDB USPAT;	2004/02/20
	[21	with (interconnection adj line\$1)	US-PGPUB; EPO; JPO;	23:25
			DERWENT;	
22	144	(liquid adj crystal adj device or lcd) and (interconnection adj line\$1)	USPAT; US-PGPUB;	2004/02/20
		and (Interconnection adj Illies))	EPO; JPO; DERWENT;	23.23
			IBM TDB	

79				
23	1	(conductive adj layer\$1)) and ((liquid	USPAT; US-PGPUB;	2004/02/20 23:25
		adj crystal adj device or lcd) and (interconnection adj line\$1))	EPO; JPO; DERWENT; IBM TDB	
24	1	<pre>(interconnection adj line\$1) and ((plurality adj capacitor\$1) same (conductive adj layer\$1))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 23:26
25	3	(liquid adj crystal adj device or lcd) and ((plurality adj capacitor\$1) same (conductive adj layer\$1))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 23:27
26	1	(plurality adj capacitor\$1) same (interconnection adj line\$1) same (conductive adj layer\$1)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 23:28
27	15	(plurality adj capacitor\$1) and (interconnection adj line\$1) and (conductive adj layer\$1)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 23:30
28	1	((plurality adj capacitor\$1) and (interconnection adj line\$1) and (conductive adj layer\$1)) and lcd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 23:28
29	3	(liquid adj crystal adj device or lcd) and ((plurality adj capacitor\$1) same (conductive adj layer\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 23:32
30	0	capacitor\$1 and 6515643.pn.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 23:36
31	0	capacitor\$1 and 5467210.pn.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 23:36
32	0	capacit\$31 and 5467210.pn.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 23:36
33	0	capacit\$3 and 5467210.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 23:38
34	2	capacit\$3 and 6569717.pn.	USPAT;	2004/02/20

US-PGPUB;

EPO; JPO; DERWENT; IBM_TDB

US-PGPUB;

EPO; JPO; DERWENT; IBM_TDB

US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

USPAT;

USPAT;

23:40

23:41

23:41

2004/02/20

2004/02/20

conduct\$3

((data or gate) and (conduct\$3 and 6172732.pn.)) and conduct\$3

(capacit\$3 and 6569717.pn.) and

35

37